

**ABSTRACT**

The invention relates to a power semiconductor module having at least one semiconductor chip (11) made of a semiconductor material and having a first and a second main electrode (12, 13), a first and a second main connection (91, 92) and a contact lamina (2) in electrical contact with the first main electrode (12) and the first main connection (92). The contact lamina (2) contains an alloying partner which can form a eutectic with the semiconductor material. According to the invention, the contact lamina is coated with an electrically conductive protective layer (31, 32) that prevents formation of a fixed material connection between the first main electrode (12) and the contact lamina (2).

(Figure 1)